

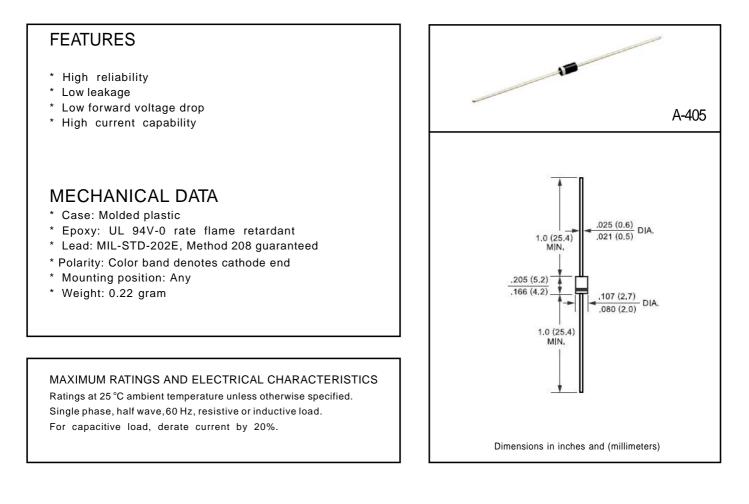
## HITANO ENTERPRISE CORP.

## RL101 THRU RL107

## TECHNICAL SPECIFICATIONS OF SILICON RECTIFIER

VOLTAGE RANGE - 50 to 1000 Volts

CURRENT - 1.0 Ampere



					1	1	1	1	1	-1
		CV/MDOI	DI 404	DI 400	DI 402	DI 404	DI 405	DI 400	DI 407	
		SYMBOL	RL101	RL102	RL103	RL104	RL105	RL106	RL107	UNITS
Maximum Recurrent Peak Reverse Voltage		Vrrm	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage		Vrms	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage		VDC	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current at TA = 55°C		lo	1.0							Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	30						Amps	
Maximum Instantaneous Forward Voltage at 1.0A DC		Vf	1.1						Volts	
Maximum DC Reverse Current	$@T_{A} = 25^{\circ}C$	_	5.0							uAmps
at Rated DC Blocking Voltage	@TA = 100°C		50							
Maximum Full Load Reverse Current Average, Full Cycle .375"(9.5mm) lead length at T $\perp$ = 75°C		– Ir	30							uAmps
Typical Junction Capacitance (Note)		CJ	15							pF
Typical Thermal Resistance		RθJA	50							°C/W
Operating and Storage Temperature Range		TJ, TSTG	-65 to + 175							°C

NOTES : Measured at 1 MHz and applied reverse voltage of 4.0 volts

## RATING AND CHARACTERISTIC CURVES (1N4001A RL101 THRU 1N4007A RL107)

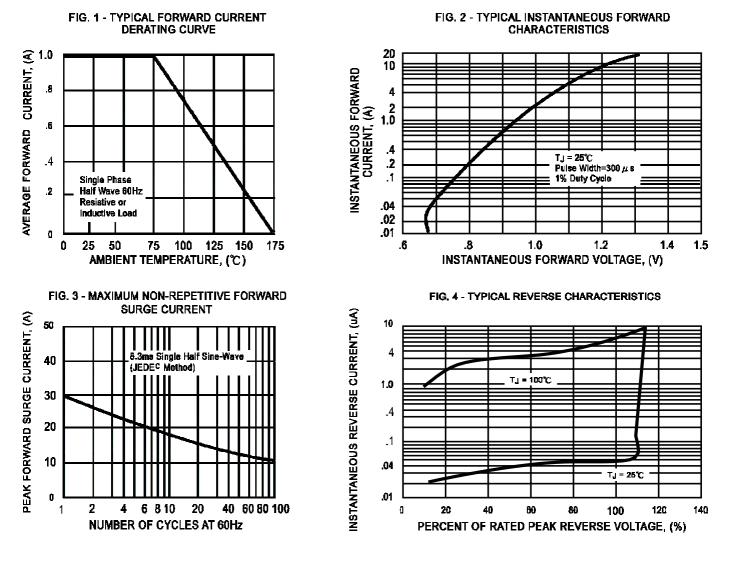


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

